

Al etching rate characterization

ICP power/W	RIE power/W	BCl ₃ flow/sccm	Cl ₂ flow/sccm	Pressure/mTorr	He pressure/Torr
250	75	50	70	180	5

Etching rate is **221 nm/min**.

Ti etching rate characterization

Gas	ICP power/W	RIE power/W	SF ₆ flow/sccm	Pressure/mtorr
SF ₆	400	100	50	25

Etching rate is **130 nm/min**.